

Small Signal Fast Switching Diodes

Features

- Silicon epitaxial planar diodes
- Electrical data identical with the devices 1N4148 and 1N4448 respectively
- Compliant to RoHS directive 2002/95/EC and in accordance to WEEE 2002/96/EC



94 9371

Applications

- Extreme fast switches

Mechanical Data

Case: MiniMELF glass case (SOD-80)

Weight: approx. 31 mg

Cathode band color: black

Packaging codes/options:

GS18/10K per 13" reel (8 mm tape), 10K/box

GS08/2.5K per 7" reel (8 mm tape), 12.5K/box

Parts Table

Part	Type differentiation	Ordering code	Marking code	Remarks
LL4148	$V_{RRM} = 100\text{ V}$, $V_F = \text{max. } 1000\text{ mV at } I_F = 50\text{ mA}$	LL4148-GS18 or LL4148-GS08	-	Tape and reel
LL4448	$V_{RRM} = 100\text{ V}$, $V_F = \text{max. } 1000\text{ mV at } I_F = 100\text{ mA}$	LL4448-GS18 or LL4448-GS08	-	Tape and reel

勝特力材料 886-3-5753170
 勝特力电子(上海) 86-21-34970699
 勝特力电子(深圳) 86-755-83298787
[Http://www.100y.com.tw](http://www.100y.com.tw)

Absolute Maximum Ratings

$T_{amb} = 25\text{ }^\circ\text{C}$, unless otherwise specified

Parameter	Test condition	Symbol	Value	Unit
Repetitive peak reverse voltage		V_{RRM}	100	V
Reverse voltage		V_R	75	V
Peak forward surge current	$t_p = 1\text{ }\mu\text{s}$	I_{FSM}	2	A
Repetitive peak forward current		I_{FRM}	500	mA
Forward continuous current		I_F	300	mA
Average forward current	$V_R = 0$	I_{FAV}	150	mA
Power dissipation		P_{tot}	500 ¹⁾	mW

Note

¹⁾ Valid provided that electrodes are kept at ambient temperature

Thermal Characteristics

$T_{amb} = 25\text{ }^\circ\text{C}$, unless otherwise specified

Parameter	Test condition	Symbol	Value	Unit
Thermal resistance junction to ambient air		R_{thJA}	300 ¹⁾	K/W
Junction temperature		T_j	175	$^\circ\text{C}$
Storage temperature range		T_{stg}	- 65 to + 175	$^\circ\text{C}$

Note

¹⁾ Valid provided that electrodes are kept at ambient temperature

Electrical Characteristics

$T_{amb} = 25\text{ }^{\circ}\text{C}$, unless otherwise specified

Parameter	Test condition	Part	Symbol	Min.	Typ.	Max.	Unit
Forward voltage	$I_F = 5\text{ mA}$	LL4448	V_F	620		720	mV
	$I_F = 50\text{ mA}$	LL4148	V_F		860	1000	mV
	$I_F = 100\text{ mA}$	LL4448	V_F		930	1000	mV
Reverse current	$V_R = 20\text{ V}$		I_R			25	nA
	$V_R = 20\text{ V}, T_j = 150\text{ }^{\circ}\text{C}$		I_R			50	μA
	$V_R = 75\text{ V}$		I_R			5	μA
Breakdown voltage	$I_R = 100\text{ }\mu\text{A}, t_p/T = 0.01,$ $t_p = 0.3\text{ ms}$		$V_{(BR)}$	100			V
Diode capacitance	$V_R = 0, f = 1\text{ MHz}, V_{HF} = 50\text{ mV}$		C_D			4	pF
Reverse recovery time	$I_F = I_R = 10\text{ mA},$ $i_R = 1\text{ mA}$		t_{rr}			8	ns
	$I_F = 10\text{ mA}, V_R = 6\text{ V},$ $i_R = 0.1 \times I_R, R_L = 100\text{ }\Omega$		t_{rr}			4	ns

Typical Characteristics

$T_{amb} = 25\text{ }^{\circ}\text{C}$, unless otherwise specified

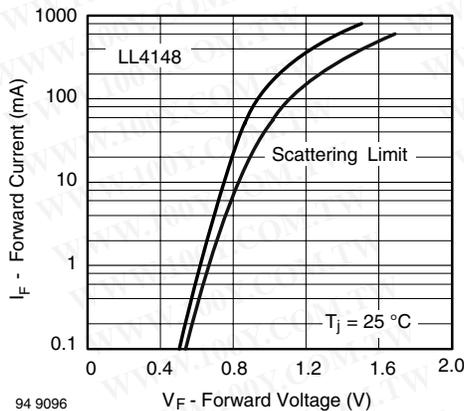


Figure 1. Forward Current vs. Forward Voltage

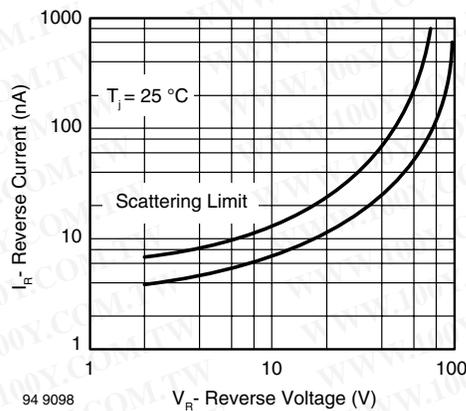


Figure 3. Reverse Current vs. Reverse Voltage

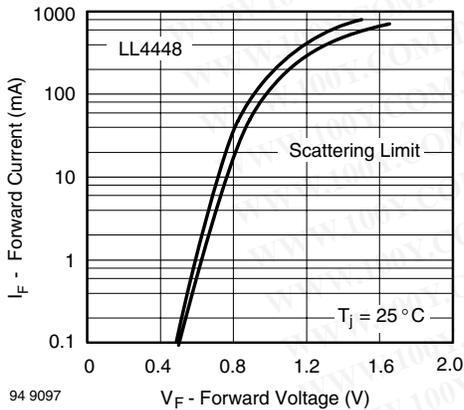


Figure 2. Forward Current vs. Forward Voltage

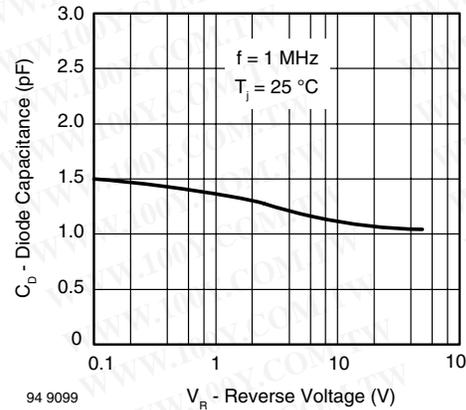
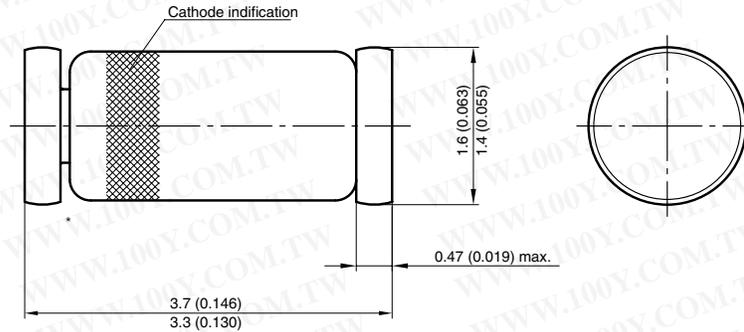


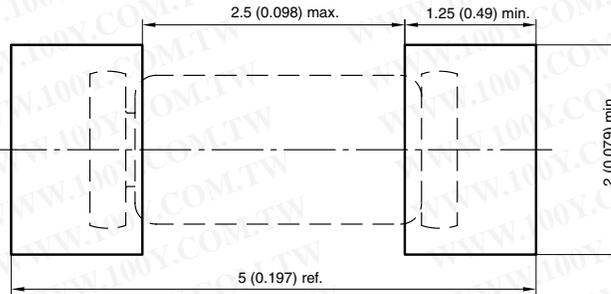
Figure 4. Diode Capacitance vs. Reverse Voltage

Package Dimensions in millimeters (inches): MiniMELF SOD-80



* The gap between plug and glass can be either on cathode or anode side

Foot print recommendation:



Document no.: 6.560-5005.01-4
 Rev. 8 - Date: 07.June.2006
 96 12070

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